AMD Xilinx - XCKU3P-L1SFVB784I Datasheet

Welcome to E-XFL.COM

Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	20340
Number of Logic Elements/Cells	355950
Total RAM Bits	31641600
Number of I/O	256
Number of Gates	-
Voltage - Supply	0.698V ~ 0.876V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	784-BFBGA, FCBGA
Supplier Device Package	784-FCBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xcku3p-l1sfvb784i

Table 1: **Absolute Maximum Ratings(1) *(Cont'd)***

Symbol	Description	Min	Max	Units
Temperature				
T_{STG}	Storage temperature (ambient).	–65	150	°C
T_{SOL}	Maximum soldering temperature.(12)	–	260	°C
T_j	Maximum junction temperature.(12)	–	125	°C

Notes:

1. Stresses beyond those listed under Absolute Maximum Ratings might cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those listed under Operating Conditions is not implied. Exposure to Absolute Maximum Ratings conditions for extended periods of time might affect device reliability.
2. V_{CCINT_IO} must be connected to V_{CCBRAM}.
3. V_{CCAUX_IO} must be connected to V_{CCAUX}.
4. The lower absolute voltage specification always applies.
5. If V_{CCO} is 3.3V, the maximum voltage is 3.4V.
6. For I/O operation, see the *UltraScale Architecture SelectIO Resources User Guide* (UG571).
7. When operating outside of the recommended operating conditions, refer to Table 4 and Table 5 for maximum overshoot and undershoot specifications.
8. AC coupled operation is not supported for RX termination = floating.
9. For GTY transceivers, DC coupled operation is not supported for RX termination = GND.
10. DC coupled operation is not supported for RX termination = programmable.
11. For more information on supported GTH or GTY transceiver terminations see the *UltraScale Architecture GTH Transceiver User Guide* (UG576) or *UltraScale Architecture GTY Transceiver User Guide* (UG578).
12. For soldering guidelines and thermal considerations, see the *UltraScale and UltraScale+ FPGAs Packaging and Pinout Specifications* (UG575).

Recommended Operating Conditions

Table 2: **Recommended Operating Conditions(1)(2)**

Symbol	Description	Min	Typ	Max	Units
FPGA Logic					
V_{CCINT}	Internal supply voltage.	0.825	0.850	0.876	V
	For -1LI and -2LE devices (V_{CCINT} = 0.72V): internal supply voltage.	0.698	0.720	0.742	V
	For -3E devices: internal supply voltage.	0.873	0.900	0.927	V
V_{CCINT_IO}(3)	Internal supply voltage for the I/O banks.	0.825	0.850	0.876	V
	For -1LI and -2LE devices (V_{CCINT} = 0.72V): internal supply voltage for the I/O banks.	0.825	0.850	0.876	V
	For -3E devices: internal supply voltage for the I/O banks.	0.873	0.900	0.927	V
V_{CCBRAM}	Block RAM supply voltage.	0.825	0.850	0.876	V
	For -3E devices: block RAM supply voltage.	0.873	0.900	0.927	V
V_{CCAUX}	Auxiliary supply voltage.	1.746	1.800	1.854	V
V_{CCO}(4)(5)	Supply voltage for HD I/O banks.	1.140	–	3.400	V
	Supply voltage for HP I/O banks.	0.950	–	1.900	V
V_{CCAUX_IO}(6)	Auxiliary I/O supply voltage.	1.746	1.800	1.854	V
V_{IN}(7)	I/O input voltage.	–0.200	–	V_{CCO} + 0.200	V
I_{IN}(8)	Maximum current through any pin in a powered or unpowered bank when forward biasing the clamp diode.	–	–	10	mA
V_{BATT}(9)	Battery voltage	1.000	–	1.890	V

Table 2: **Recommended Operating Conditions(1)(2) *(Cont'd)***

Symbol	Description	Min	Typ	Max	Units
GTH or GTY Transceiver					
$V_{MGTAVCC}$(10)	Analog supply voltage for the GTH or GTY transceiver.	0.873	0.900	0.927	V
$V_{MGTAVTT}$(10)	Analog supply voltage for the GTH or GTY transmitter and receiver termination circuits.	1.164	1.200	1.236	V
$V_{MGTVCCAUX}$(10)	Auxiliary analog QPLL voltage supply for the transceivers.	1.746	1.800	1.854	V
$V_{MGTAVTTRCAL}$(10)	Analog supply voltage for the resistor calibration circuit of the GTH or GTY transceiver column.	1.164	1.200	1.236	V
SYSMON					
V_{CCADC}	SYSMON supply relative to GNDADC.	1.746	1.800	1.854	V
V_{REFP}	SYSMON externally supplied reference voltage relative to GNDADC.	1.200	1.250	1.300	V
Temperature					
T_j(12)	Junction temperature operating range for extended (E) temperature devices.(11)	0	–	100	°C
	Junction temperature operating range for industrial (I) temperature devices.	–40	–	100	°C
	Junction temperature operating range for eFUSE programming.(13)	–40	–	125	°C

Notes:

1. All voltages are relative to GND.
2. For the design of the power distribution system consult *UltraScale Architecture PCB Design Guide* (UG583).
3. V_{CCINT_IO} must be connected to V_{CCBRAM}.
4. For V_{CCO_0}, the minimum recommended operating voltage for power on and during configuration is 1.425V. After configuration, data is retained even if V_{CCO} drops to 0V.
5. Includes V_{CCO} of 1.0V (HP I/O only), 1.2V, 1.35V, 1.5V, 1.8V, 2.5V (HD I/O only) at ±5%, and 3.3V (HD I/O only) at +3/–5%.
6. V_{CCAUX_IO} must be connected to V_{CCAUX}.
7. The lower absolute voltage specification always applies.
8. A total of 200 mA per bank should not be exceeded.
9. If battery is not used, connect V_{BATT} to either GND or V_{CCAUX}.
10. Each voltage listed requires filtering as described in *UltraScale Architecture GTH Transceiver User Guide* (UG576) or *UltraScale Architecture GTY Transceiver User Guide* (UG578).
11. Devices labeled with the speed/temperature grade of -2LE normally operate under Extended (E) temperature grade specifications with a maximum junction temperature of 100°C. However, E temperature grade devices can operate for a for a limited time at a junction temperature of 110°C. Timing parameters adhere to the same speed file at 110°C as they do at 100°C, regardless of operating voltage (nominal voltage of 0.85V or a low-voltage of 0.72V). Operation at Tj = 110°C is limited to 1% of the device lifetime and can occur sequentially or at regular intervals as long as the total time does not exceed 1% of the device lifetime.
12. Xilinx recommends measuring the Tj of a device using the system monitor as described in the *UltraScale Architecture System Monitor User Guide* (UG580). The SYSMON temperature measurement errors (that are described in Table 76) must be accounted for in your design. For example, by using an external reference of 1.25V, when SYSMON reports 97°C, there is a measurement error ±3°C. A reading of 97°C is considered the maximum adjusted Tj (100°C – 3°C = 97°C).
13. Do not program eFUSE during device configuration (e.g., during configuration, during configuration readback, or when readback CRC is active).

DC Characteristics Over Recommended Operating Conditions

Table 3: **DC Characteristics Over Recommended Operating Conditions**

Symbol	Description	Min	Typ(1)	Max	Units
V_{DRINT}	Data retention V_{CCINT} voltage (below which configuration data might be lost).	0.68	–	–	V
V_{DRAUX}	Data retention V_{CCAUX} voltage (below which configuration data might be lost).	1.5	–	–	V
I_{REF}	V_{REF} leakage current per pin.	–	–	15	µA
I_L	Input or output leakage current per pin (sample-tested).(2)	–	–	15	µA
C_{IN}(3)	Die input capacitance at the pad (HP I/O).	–	–	3.1	pF
	Die input capacitance at the pad (HD I/O).	–	–	4.75	pF
I_{RPU}	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 3.3V.	75	–	190	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 2.5V.	50	–	169	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 1.8V.	60	–	120	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 1.5V.	30	–	120	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 1.2V.	10	–	100	µA
I_{RPD}	Pad pull-down (when selected) at V_{IN} = 3.3V.	60	–	200	µA
	Pad pull-down (when selected) at V_{IN} = 1.8V.	29	–	120	µA
$I_{CCADCON}$	Analog supply current for the SYSMON circuits in the power-up state.	–	–	8	mA
$I_{CCADCOFF}$	Analog supply current for the SYSMON circuits in the power-down state.	–	–	1.5	mA
I_{BATT}(4)(5)	Battery supply current at V_{BATT} = 1.89V.	–	–	650	nA
	Battery supply current at V_{BATT} = 1.20V.	–	–	150	nA
I_{PFS}(6)	V_{CCAUX} additional supply current during eFUSE programming.	–	–	115	mA
Calibrated programmable on-die termination (DCI) in HP I/O banks(7) (measured per JEDEC specification).					
R(9)	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 where ODT = RTT_40.	–10%(8)	40	+10%(8)	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 where ODT = RTT_48.	–10%(8)	48	+10%(8)	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 where ODT = RTT_60.	–10%(8)	60	+10%(8)	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_40.	–10%(8)	40	+10%(8)	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_48.	–10%(8)	48	+10%(8)	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_60.	–10%(8)	60	+10%(8)	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_120.	–10%(8)	120	+10%(8)	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_240.	–10%(8)	240	+10%(8)	Ω

Table 3: **DC Characteristics Over Recommended Operating Conditions *(Cont'd)***

Symbol	Description	Min	Typ(1)	Max	Units
Uncalibrated programmable on-die termination in HP I/O banks (measured per JEDEC specification).					
R(9)	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where ODT = RTT_40.	–50%	40	+50%	Ω
	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where ODT = RTT_48.	–50%	48	+50%	Ω
	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where ODT = RTT_60.	–50%	60	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_40.	–50%	40	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_48.	–50%	48	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_60.	–50%	60	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_120.	–50%	120	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_240.	–50%	240	+50%	Ω
Uncalibrated programmable on-die termination in HD I/O banks (measured per JEDEC specification).					
R(9)	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where ODT = RTT_48.	–50%	48	+50%	Ω
Internal V_{REF}	50% V_{CCO}	V_{CCO} x 0.49	V_{CCO} x 0.50	V_{CCO} x 0.51	V
	70% V_{CCO}	V_{CCO} x 0.69	V_{CCO} x 0.70	V_{CCO} x 0.71	V
Differential termination	Programmable differential termination (TERM_100) for HP I/O banks.	–35%	100	+35%	Ω
n	Temperature diode ideality factor.	–	1.026	–	–
r	Temperature diode series resistance.	–	2	–	Ω

Notes:

1. Typical values are specified at nominal voltage, 25°C.
2. For HP I/O banks with a V_{CCO} of 1.8V and separated V_{CCO} and V_{CCAUX_IO} power supplies, the I_L maximum current is 70 µA.
3. This measurement represents the die capacitance at the pad, not including the package.
4. Maximum value specified for worst case process at 25°C.
5. I_{BATT} is measured when the battery-backed RAM (BBRAM) is enabled.
6. Do not program eFUSE during device configuration (e.g., during configuration, during configuration readback, or when readback CRC is active).
7. If VRP resides at a different bank (DCI cascade), the range increases to ±15%.
8. VRP resistor tolerance is (240Ω ±1%)
9. On-die input termination resistance, for more information see the *UltraScale Architecture SelectIO Resources User Guide* (UG571).

V_{IN} Maximum Allowed AC Voltage Overshoot and Undershoot

Table 4: **V_{IN} Maximum Allowed AC Voltage Overshoot and Undershoot for HD I/O Banks(1)**

AC Voltage Overshoot	% of UI at –40°C to 100°C	AC Voltage Undershoot	% of UI at –40°C to 100°C
V_{CCO} + 0.30	100%	–0.30	100%
V_{CCO} + 0.35	100%	–0.35	90%
V_{CCO} + 0.40	100%	–0.40	78%
V_{CCO} + 0.45	100%	–0.45	40%
V_{CCO} + 0.50	100%	–0.50	24%
V_{CCO} + 0.55	100%	–0.55	18.0%
V_{CCO} + 0.60	100%	–0.60	13.0%
V_{CCO} + 0.65	100%	–0.65	10.8%
V_{CCO} + 0.70	92%	–0.70	9.0%
V_{CCO} + 0.75	92%	–0.75	7.0%
V_{CCO} + 0.80	92%	–0.80	6.0%
V_{CCO} + 0.85	92%	–0.85	5.0%
V_{CCO} + 0.90	92%	–0.90	4.0%
V_{CCO} + 0.95	92%	–0.95	2.5%

Notes:

1. A total of 200 mA per bank should not be exceeded.

Table 5: **V_{IN} Maximum Allowed AC Voltage Overshoot and Undershoot for HP I/O Banks(1)(2)**

AC Voltage Overshoot	% of UI at –40°C to 100°C	AC Voltage Undershoot	% of UI at –40°C to 100°C
V_{CCO} + 0.30	100%	–0.30	100%
V_{CCO} + 0.35	100%	–0.35	90%
V_{CCO} + 0.40	92%	–0.40	92%
V_{CCO} + 0.45	50%	–0.45	50%
V_{CCO} + 0.50	20%	–0.50	20%
V_{CCO} + 0.55	10%	–0.55	10%
V_{CCO} + 0.60	6%	–0.60	6%
V_{CCO} + 0.65	2%	–0.65	2%
V_{CCO} + 0.70	2%	–0.70	2%

Notes:

1. A total of 200 mA per bank should not be exceeded.
2. For UI smaller than 20 µs.

Speed Grade Designations

Since individual family members are produced at different times, the migration from one category to another depends completely on the status of the fabrication process for each device. Table 21 correlates the current status of the Kintex UltraScale+ FPGAs on a per speed grade basis.

Table 21: **Speed Grade Designations by Device**

Device	Speed Grade, Temperature Ranges, and V_{CCINT} Operating Voltages		
	Advance	**Preliminary**	**Production**
XCKU3P	-3E (V_{CCINT} = 0.90V) -2LE (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.72V)(1) -1LI (V_{CCINT} = 0.85V), -1LI (V_{CCINT} = 0.72V)(1)		-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V) -1I (V_{CCINT} = 0.85V)
XCKU5P	-3E (V_{CCINT} = 0.90V) -2LE (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.72V)(1) -1LI (V_{CCINT} = 0.85V), -1LI (V_{CCINT} = 0.72V)(1)		-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V) -1I (V_{CCINT} = 0.85V)
XCKU9P	-3E (V_{CCINT} = 0.90V) -2LE (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.72V)(1) -1LI (V_{CCINT} = 0.85V), -1LI (V_{CCINT} = 0.72V)(1)	-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V) -1I (V_{CCINT} = 0.85V)	
XCKU11P	-3E (V_{CCINT} = 0.90V) -2E (V_{CCINT} = 0.85V), -2I (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V)(1), -1LI (V_{CCINT} = 0.72V)(1)		
XCKU13P	-3E (V_{CCINT} = 0.90V) -2E (V_{CCINT} = 0.85V), -2I (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V)(1), -1LI (V_{CCINT} = 0.72V)(1)		
XCKU15P	-3E (V_{CCINT} = 0.90V) -2E (V_{CCINT} = 0.85V), -2I (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V)(1), -1LI (V_{CCINT} = 0.72V)(1)		

Notes:

1. The lowest power -1L and -2L devices, where V_{CCINT} = 0.72V, are listed in the Vivado Design Suite as -1LV and -2LV respectively.

Table 25: **MIPI D-PHY Performance**

Description	I/O Bank Type	Speed Grade and V_{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
MIPI D-PHY transmitter or receiver.	HP	1500	1500	1260	1260	1260	Mb/s

Table 26: **LVDS Native-Mode 1000BASE-X Support(1)**

Description	I/O Bank Type	Speed Grade and V_{CCINT} Operating Voltages				
		0.90V	0.85V		0.72V	
		-3	-2	-1	-2	-1
1000BASE-X	HP	Yes				

Notes:

1. 1000BASE-X support is based on the *IEEE Standard for CSMA/CD Access Method and Physical Layer Specifications* (IEEE Std 802.3-2008).

Table 27 provides the maximum data rates for applicable memory standards using the Kintex UltraScale+ FPGA memory PHY. Refer to Memory Interfaces for the complete list of memory interface standards supported and detailed specifications. The final performance of the memory interface is determined through a complete design implemented in the Vivado Design Suite, following guidelines in the *UltraScale Architecture PCB Design Guide* (UG583), electrical analysis, and characterization of the system.

Table 27: **Maximum Physical Interface (PHY) Rate for Memory Interfaces**

Memory Standard	Package	DRAM Type	Speed Grade and V_{CCINT} Operating Voltages					Units
			0.90V	0.85V		0.72V		
			-3	-2	-1	-2	-1	
DDR4	All FFV packages	Single rank component	2666	2666	2400	2400	2133	Mb/s
		1 rank DIMM(1)(2)(3)	2400	2400	2133	2133	1866	Mb/s
		2 rank DIMM(1)(4)	2133	2133	1866	1866	1600	Mb/s
		4 rank DIMM(1)(5)	1600	1600	1333	1333	N/A	Mb/s
	SFVB784	Single rank component	2400	2400	2133	2133	1866	Mb/s
		1 rank DIMM(1)(2)	2133	2133	1866	1866	1600	Mb/s
		2 rank DIMM(1)(4)	1866	1866	1600	1600	1600	Mb/s
DDR3	All FFV packages	Single rank component	2133	2133	2133	2133	1866	Mb/s
		1 rank DIMM(1)(2)	1866	1866	1866	1866	1600	Mb/s
		2 rank DIMM(1)(4)	1600	1600	1600	1600	1333	Mb/s
		4 rank DIMM(1)(5)	1066	1066	1066	1066	800	Mb/s
	SFVB784	Single rank component	1866	1866	1866	1866	1600	Mb/s
		1 rank DIMM(1)(2)	1600	1600	1600	1600	1600	Mb/s
		2 rank DIMM(1)(4)	1600	1600	1600	1600	1333	Mb/s
		4 rank DIMM(1)(5)	1066	1066	1066	1066	800	Mb/s

Table 29: **IOB High Performance (HP) Switching Characteristics *(Cont'd)***

I/O Standards	$T_{INBUF_DELAY_PAD_I}$					$T_{OUTBUF_DELAY_O_PAD}$					$T_{OUTBUF_DELAY_TD_PAD}$					Units
	0.90V	0.85V		0.72V		0.90V	0.85V		0.72V		0.90V	0.85V		0.72V		
	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	
LVCMOS18_F_8	0.418	0.418	0.445	0.418	0.445	0.573	0.573	0.600	0.573	0.600	0.733	0.733	0.767	0.733	0.767	ns
LVCMOS18_M_12	0.418	0.418	0.445	0.418	0.445	0.640	0.640	0.678	0.640	0.678	0.670	0.670	0.709	0.670	0.709	ns
LVCMOS18_M_2	0.418	0.418	0.445	0.418	0.445	0.798	0.798	0.822	0.798	0.822	0.991	0.991	1.016	0.991	1.016	ns
LVCMOS18_M_4	0.418	0.418	0.445	0.418	0.445	0.664	0.664	0.693	0.664	0.693	0.798	0.798	0.836	0.798	0.836	ns
LVCMOS18_M_6	0.418	0.418	0.445	0.418	0.445	0.629	0.629	0.663	0.629	0.663	0.735	0.735	0.775	0.735	0.775	ns
LVCMOS18_M_8	0.418	0.418	0.445	0.418	0.445	0.626	0.626	0.661	0.626	0.661	0.705	0.705	0.746	0.705	0.746	ns
LVCMOS18_S_12	0.418	0.418	0.445	0.418	0.445	0.795	0.795	0.861	0.795	0.861	0.683	0.683	0.721	0.683	0.721	ns
LVCMOS18_S_2	0.418	0.418	0.445	0.418	0.445	0.862	0.862	0.897	0.862	0.897	1.076	1.076	1.098	1.076	1.098	ns
LVCMOS18_S_4	0.418	0.418	0.445	0.418	0.445	0.716	0.716	0.758	0.716	0.758	0.829	0.829	0.872	0.829	0.872	ns
LVCMOS18_S_6	0.418	0.418	0.445	0.418	0.445	0.682	0.682	0.724	0.682	0.724	0.724	0.724	0.762	0.724	0.762	ns
LVCMOS18_S_8	0.418	0.418	0.445	0.418	0.445	0.707	0.707	0.760	0.707	0.760	0.709	0.709	0.745	0.709	0.745	ns
LVDCI_15_F	0.425	0.425	0.462	0.425	0.462	0.426	0.426	0.443	0.426	0.443	0.548	0.548	0.581	0.548	0.581	ns
LVDCI_15_M	0.425	0.425	0.462	0.425	0.462	0.553	0.553	0.582	0.553	0.582	0.645	0.645	0.685	0.645	0.685	ns
LVDCI_15_S	0.425	0.425	0.462	0.425	0.462	0.749	0.749	0.803	0.749	0.803	0.821	0.821	0.890	0.821	0.890	ns
LVDCI_18_F	0.414	0.414	0.447	0.414	0.447	0.441	0.441	0.459	0.441	0.459	0.560	0.560	0.589	0.560	0.589	ns
LVDCI_18_M	0.414	0.414	0.447	0.414	0.447	0.554	0.554	0.585	0.554	0.585	0.644	0.644	0.683	0.644	0.683	ns
LVDCI_18_S	0.414	0.414	0.447	0.414	0.447	0.760	0.760	0.818	0.760	0.818	0.837	0.837	0.899	0.837	0.899	ns
LVDS	0.539	0.539	0.620	0.539	0.620	0.626	0.626	0.662	0.626	0.662	960.447	960.447	960.447	960.447	960.447	ns
MIPI_DPHY_DCI_HS	0.386	0.386	0.415	0.386	0.415	0.502	0.502	0.522	0.502	0.522	N/A	N/A	N/A	N/A	N/A	ns
MIPI_DPHY_DCI_LP	8.438	8.438	8.792	8.438	8.792	0.914	0.914	0.937	0.914	0.937	N/A	N/A	N/A	N/A	N/A	ns
POD10_DCI_F	0.408	0.408	0.430	0.408	0.430	0.425	0.425	0.444	0.425	0.444	0.555	0.555	0.584	0.555	0.584	ns
POD10_DCI_M	0.408	0.408	0.430	0.408	0.430	0.542	0.542	0.571	0.542	0.571	0.640	0.640	0.681	0.640	0.681	ns
POD10_DCI_S	0.408	0.408	0.430	0.408	0.430	0.754	0.754	0.815	0.754	0.815	0.850	0.850	0.917	0.850	0.917	ns
POD10_F	0.407	0.407	0.430	0.407	0.430	0.438	0.438	0.459	0.438	0.459	0.569	0.569	0.601	0.569	0.601	ns
POD10_M	0.407	0.407	0.430	0.407	0.430	0.538	0.538	0.568	0.538	0.568	0.630	0.630	0.667	0.630	0.667	ns
POD10_S	0.407	0.407	0.430	0.407	0.430	0.766	0.766	0.821	0.766	0.821	0.836	0.836	0.894	0.836	0.894	ns
POD12_DCI_F	0.409	0.409	0.431	0.409	0.431	0.425	0.425	0.443	0.425	0.443	0.558	0.558	0.586	0.558	0.586	ns
POD12_DCI_M	0.409	0.409	0.431	0.409	0.431	0.543	0.543	0.572	0.543	0.572	0.638	0.638	0.678	0.638	0.678	ns
POD12_DCI_S	0.409	0.409	0.431	0.409	0.431	0.772	0.772	0.822	0.772	0.822	0.862	0.862	0.929	0.862	0.929	ns
POD12_F	0.409	0.409	0.431	0.409	0.431	0.455	0.455	0.476	0.455	0.476	0.595	0.595	0.626	0.595	0.626	ns
POD12_M	0.409	0.409	0.431	0.409	0.431	0.551	0.551	0.582	0.551	0.582	0.641	0.641	0.679	0.641	0.679	ns
POD12_S	0.409	0.409	0.431	0.409	0.431	0.767	0.767	0.817	0.767	0.817	0.832	0.832	0.889	0.832	0.889	ns
SLVS_400_18	0.539	0.539	0.620	0.539	0.620	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	ns
SSTL12_DCI_F	0.381	0.381	0.399	0.381	0.399	0.425	0.425	0.443	0.425	0.443	0.558	0.558	0.586	0.558	0.586	ns
SSTL12_DCI_M	0.381	0.381	0.399	0.381	0.399	0.557	0.557	0.587	0.557	0.587	0.654	0.654	0.694	0.654	0.694	ns
SSTL12_DCI_S	0.381	0.381	0.399	0.381	0.399	0.754	0.754	0.803	0.754	0.803	0.842	0.842	0.908	0.842	0.908	ns
SSTL12_F	0.403	0.403	0.403	0.403	0.403	0.412	0.412	0.430	0.412	0.430	0.538	0.538	0.566	0.538	0.566	ns
SSTL12_M	0.403	0.403	0.403	0.403	0.403	0.553	0.553	0.584	0.553	0.584	0.641	0.641	0.676	0.641	0.676	ns
SSTL12_S	0.403	0.403	0.403	0.403	0.403	0.758	0.758	0.808	0.758	0.808	0.823	0.823	0.879	0.823	0.879	ns
SSTL135_DCI_F	0.366	0.366	0.399	0.366	0.399	0.411	0.411	0.428	0.411	0.428	0.537	0.537	0.565	0.537	0.565	ns
SSTL135_DCI_M	0.366	0.366	0.399	0.366	0.399	0.551	0.551	0.582	0.551	0.582	0.645	0.645	0.685	0.645	0.685	ns

Output Delay Measurement Methodology

Output delays are measured with short output traces. Standard termination was used for all testing. The propagation delay of the trace is characterized separately and subtracted from the final measurement, and is therefore not included in the generalized test setups shown in Figure 1 and Figure 2.

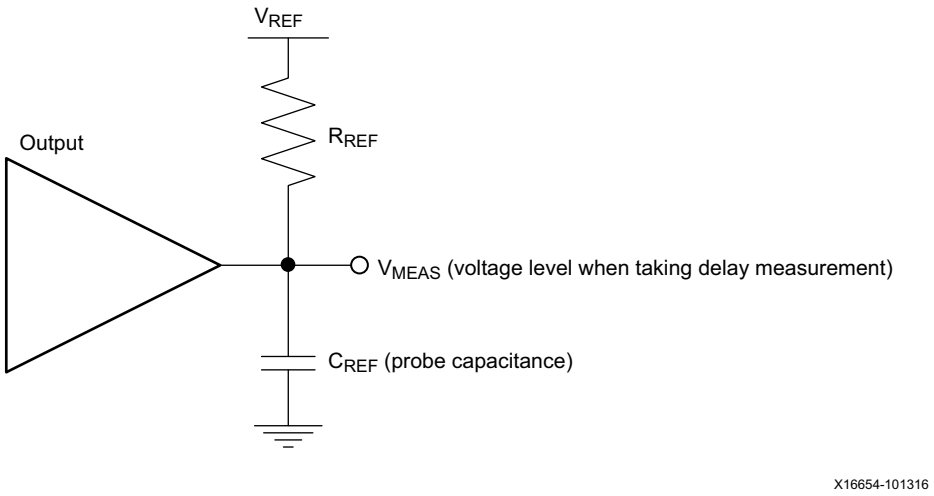

Figure 1: **Single-Ended Test Setup**

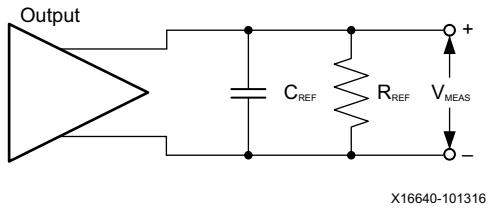

Figure 2: **Differential Test Setup**

Parameters V_{REF}, R_{REF}, C_{REF}, and V_{MEAS} fully describe the test conditions for each I/O standard. The most accurate prediction of propagation delay in any given application can be obtained through IBIS simulation, using this method:

1. Simulate the output driver of choice into the generalized test setup using values from Table 32.
2. Record the time to V_{MEAS}.
3. Simulate the output driver of choice into the actual PCB trace and load using the appropriate IBIS model or capacitance value to represent the load.
4. Record the time to V_{MEAS}.
5. Compare the results of step 2 and step 4. The increase or decrease in delay yields the actual propagation delay of the PCB trace.

Package Parameter Guidelines

The parameters in this section provide the necessary values for calculating timing budgets for clock transmitter and receiver data-valid windows.

Table 46: **Package Skew**

Symbol	Description	Device	Package	Value	Units
PKGSKEW	Package Skew	XCKU3P	SFVB784	75	ps
			FFVA676	136	ps
			FFVB676	69	ps
			FFVD900	179	ps
		XCKU5P	SFVB784	75	ps
			FFVA676	136	ps
			FFVB676	69	ps
			FFVD900	179	ps
		XCKU9P	FFVE900	212	ps
		XCKU11P	FFVD900		ps
			FFVA1156		ps
			FFVE1517		ps
		XCKU13P	FFVE900	197	ps
		XCKU15P	FFVA1156	203	ps
			FFVE1517	167	ps
			FFVA1760	191	ps
			FFVE1760	172	ps

Notes:

1. These values represent the worst-case skew between any two SelectIO resources in the package: shortest delay to longest delay from die pad to ball.
2. Package delay information is available for these device/package combinations. This information can be used to deskew the package.

GTH Transceiver Specifications

The *UltraScale Architecture and Product Overview* (DS890) lists the Kintex UltraScale+ FPGAs that include the GTH transceivers.

GTH Transceiver DC Input and Output Levels

Table 47 summarizes the DC specifications of the GTH transceivers in the Kintex UltraScale+ FPGAs. Consult the *UltraScale Architecture GTH Transceiver User Guide* (UG576) for further information.

Table 47: **GTH Transceiver DC Specifications**

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
DV_{PPIN}	Differential peak-to-peak input voltage (external AC coupled).	>10.3125 Gb/s	150	–	1250	mV
		6.6 Gb/s to 10.3125 Gb/s	150	–	1250	mV
		≤ 6.6 Gb/s	150	–	2000	mV
V_{IN}	Single-ended input voltage. Voltage measured at the pin referenced to GND.	DC coupled $V_{MGTAVTT}$ = 1.2V	–400	–	$V_{MGTAVTT}$	mV
V_{CMIN}	Common mode input voltage.	DC coupled $V_{MGTAVTT}$ = 1.2V	–	2/3 $V_{MGTAVTT}$	–	mV
D_{VPPOUT}	Differential peak-to-peak output voltage.(1)	Transmitter output swing is set to 11111	800	–	–	mV
$V_{CMOUTDC}$	Common mode output voltage: DC coupled (equation based).	When remote RX is terminated to GND	$V_{MGTAVTT}/2 - D_{VPPOUT}/4$			mV
		When remote RX termination is floating	$V_{MGTAVTT} - D_{VPPOUT}/2$			mV
		When remote RX is terminated to V_{RX_TERM}(2)	$V_{MGTAVTT} - \left(\frac{D_{VPPOUT}}{4} - \left(\frac{V_{MGTAVTT} - V_{RX_TERM}}{2}\right)\right)$			mV
$V_{CMOUTAC}$	Common mode output voltage: AC coupled (equation based).		$V_{MGTAVTT} - D_{VPPOUT}/2$			mV
R_{IN}	Differential input resistance.		–	100	–	Ω
R_{OUT}	Differential output resistance.		–	100	–	Ω
T_{OSKEW}	Transmitter output pair (TXP and TXN) intra-pair skew (All packages).		–	–	10	ps
C_{EXT}	Recommended external AC coupling capacitor.(3)		–	100	–	nF

Notes:

1. The output swing and pre-emphasis levels are programmable using the attributes discussed in the *UltraScale Architecture GTH Transceiver User Guide* (UG576), and can result in values lower than reported in this table.
2. V_{RX_TERM} is the remote RX termination voltage.
3. Other values can be used as appropriate to conform to specific protocols and standards.

Table 56: **GTH Transceiver Transmitter Switching Characteristics *(Cont'd)***

Symbol	Description	Condition	Min	Typ	Max	Units
$T_{J2.5}$	Total jitter(3)(4)	2.5 Gb/s(6)	–	–	0.20	UI
$D_{J2.5}$	Deterministic jitter(3)(4)		–	–	0.10	UI
$T_{J1.25}$	Total jitter(3)(4)	1.25 Gb/s(7)	–	–	0.15	UI
$D_{J1.25}$	Deterministic jitter(3)(4)		–	–	0.06	UI
T_{J500}	Total jitter(3)(4)	500 Mb/s(8)	–	–	0.10	UI
D_{J500}	Deterministic jitter(3)(4)		–	–	0.03	UI

Notes:

1. Using same REFCLK input with TX phase alignment enabled for up to four consecutive transmitters (one fully populated GTH Quad) at the maximum line rate.
2. Using QPLL_FBDIV = 40, 20-bit internal data width. These values are NOT intended for protocol specific compliance determinations.
3. Using CPLL_FBDIV = 2, 20-bit internal data width. These values are NOT intended for protocol specific compliance determinations.
4. All jitter values are based on a bit-error ratio of 10^{-12}.
5. CPLL frequency at 3.2 GHz and TXOUT_DIV = 2.
6. CPLL frequency at 2.5 GHz and TXOUT_DIV = 2.
7. CPLL frequency at 2.5 GHz and TXOUT_DIV = 4.
8. CPLL frequency at 2.0 GHz and TXOUT_DIV = 8.

Table 57: **GTH Transceiver Receiver Switching Characteristics**

Symbol	Description	Condition	Min	Typ	Max	Units
F_{GTHRX}	Serial data rate		0.500	–	F_{GTHMAX}	Gb/s
R_{XSST}	Receiver spread-spectrum tracking(1)	Modulated at 33 kHz	–5000	–	0	ppm
R_{XRL}	Run length (CID)		–	–	256	UI
$R_{XPPMTOL}$	Data/REFCLK PPM offset tolerance	Bit rates ≤ 6.6 Gb/s	–1250	–	1250	ppm
		Bit rates > 6.6 Gb/s and ≤ 8.0 Gb/s	–700	–	700	ppm
		Bit rates > 8.0 Gb/s	–200	–	200	ppm
SJ Jitter Tolerance(2)						
$J_{T_SJ16.375}$	Sinusoidal jitter (QPLL)(3)	16.375 Gb/s	0.30	–	–	UI
$J_{T_SJ15.1}$	Sinusoidal jitter (QPLL)(3)	15.1 Gb/s	0.30	–	–	UI
$J_{T_SJ14.1}$	Sinusoidal jitter (QPLL)(3)	14.1 Gb/s	0.30	–	–	UI
$J_{T_SJ13.1}$	Sinusoidal jitter (QPLL)(3)	13.1 Gb/s	0.30	–	–	UI
$J_{T_SJ12.5}$	Sinusoidal jitter (QPLL)(3)	12.5 Gb/s	0.30	–	–	UI
$J_{T_SJ11.3}$	Sinusoidal jitter (QPLL)(3)	11.3 Gb/s	0.30	–	–	UI
$J_{T_SJ10.32_QPLL}$	Sinusoidal jitter (QPLL)(3)	10.32 Gb/s	0.30	–	–	UI
$J_{T_SJ10.32_CPLL}$	Sinusoidal jitter (CPLL)(3)	10.32 Gb/s	0.30	–	–	UI
$J_{T_SJ9.953_QPLL}$	Sinusoidal jitter (QPLL)(3)	9.953 Gb/s	0.30	–	–	UI
$J_{T_SJ9.953_CPLL}$	Sinusoidal jitter (CPLL)(3)	9.953 Gb/s	0.30	–	–	UI
$J_{T_SJ8.0}$	Sinusoidal jitter (QPLL)(3)	8.0 Gb/s	0.42	–	–	UI
$J_{T_SJ6.6_CPLL}$	Sinusoidal jitter (CPLL)(3)	6.6 Gb/s	0.44	–	–	UI
$J_{T_SJ5.0}$	Sinusoidal jitter (CPLL)(3)	5.0 Gb/s	0.44	–	–	UI
$J_{T_SJ4.25}$	Sinusoidal jitter (CPLL)(3)	4.25 Gb/s	0.44	–	–	UI
$J_{T_SJ3.2}$	Sinusoidal jitter (CPLL)(3)	3.2 Gb/s(4)	0.45	–	–	UI

Table 58: **GTH Transceiver Protocol List**

Protocol	Specification	Serial Rate (Gb/s)	Electrical Compliance
CAUI-10	IEEE 802.3-2012	10.3125	Compliant
nPPI	IEEE 802.3-2012	10.3125	Compliant
10GBASE-KR(1)	IEEE 802.3-2012	10.3125	Compliant
40GBASE-KR	IEEE 802.3-2012	10.3125	Compliant
SFP+	SFF-8431 (SR and LR)	9.95328–11.10	Compliant
XFP	INF-8077i, revision 4.5	10.3125	Compliant
RXAUI	CEI-6G-SR	6.25	Compliant
XAUI	IEEE 802.3-2012	3.125	Compliant
1000BASE-X	IEEE 802.3-2012	1.25	Compliant
5.0G Ethernet	IEEE 802.3bx (PAR)	5	Compliant
2.5G Ethernet	IEEE 802.3bx (PAR)	2.5	Compliant
HiGig, HiGig+, HiGig2	IEEE 802.3-2012	3.74, 6.6	Compliant
OTU2	ITU G.8251	10.709225	Compliant
OTU4 (OTL4.10)	OIF-CEI-11G-SR	11.180997	Compliant
OC-3/12/48/192	GR-253-CORE	0.1555–9.956	Compliant
TFI-5	OIF-TFI5-0.1.0	2.488	Compliant
Interlaken	OIF-CEI-6G, OIF-CEI-11G-SR	4.25–12.5	Compliant
PCIe Gen1, 2, 3	PCI Express base 3.0	2.5, 5.0, and 8.0	Compliant
SDI(2)	SMPTE 424M-2006	0.27–2.97	Compliant
UHD-SDI(2)	SMPTE ST-2081 6G, SMPTE ST-2082 12G	6 and 12	Compliant
Hybrid memory cube (HMC)	HMC-15G-SR	10, 12.5, and 15.0	Compliant
MoSys Bandwidth Engine	CEI-11-SR and CEI-11-SR (overclocked)	10.3125, 15.5	Compliant
CPRI	CPRI_v_6_1_2014-07-01	0.6144–12.165	Compliant
HDMI(2)	HDMI 2.0	All	Compliant
Passive optical network (PON)	10G-EPON, 1G-EPON, NG-PON2, XG-PON, and 2.5G-PON	0.155–10.3125	Compliant
JESD204a/b	OIF-CEI-6G, OIF-CEI-11G	3.125–12.5	Compliant
Serial RapidIO	RapidIO specification 3.1	1.25–10.3125	Compliant
DisplayPort(2)	DP 1.2B CTS	1.62–5.4	Compliant
Fibre channel	FC-PI-4	1.0625–14.025	Compliant
SATA Gen1, 2, 3	Serial ATA revision 3.0 specification	1.5, 3.0, and 6.0	Compliant
SAS Gen1, 2, 3	T10/BSR INCITS 519	3.0, 6.0, and 12.0	Compliant
SFI-5	OIF-SFI5-01.0	0.625–12.5	Compliant
Aurora	CEI-6G, CEI-11G-LR	up to 11.180997	Compliant

Notes:
1. The transition time of the transmitter is faster than the IEEE Std 802.3-2012 specification.
2. This protocol requires external circuitry to achieve compliance.

Table 67: **GTY Transceiver User Clock Switching Characteristics(1) *(Cont'd)***

Symbol	Description	Data Width Conditions (Bit)		Speed Grade and V_{CCINT} Operating Voltages					Units
				0.90V	0.85V		0.72V		
		Internal Logic	Interconnect Logic	-3(2)	-2(2)(3)	-1(4)(5)	-2(3)	-1(5)	
F_{TXIN2}	TXUSRCLK2(6) maximum frequency	16	16	511.719	511.719	390.625	390.625	322.266	MHz
		16	32	255.859	255.859	195.313	195.313	161.133	MHz
		32	32	511.719	511.719	390.625	390.625	322.266	MHz
		32	64	255.859	255.859	195.313	195.313	161.133	MHz
		64	64	511.719	440.781	402.832	402.832	195.313	MHz
		64	128	255.859	220.391	201.416	201.416	97.656	MHz
		20	20	409.375	409.375	312.500	312.500	257.813	MHz
		20	40	204.688	204.688	156.250	156.250	128.906	MHz
		40	40	409.375	409.375	312.500	350.000	257.813	MHz
		40	80	204.688	204.688	156.250	175.000	128.906	MHz
		80	80	409.375	352.625	322.266	352.625	156.250	MHz
		80	160	204.688	176.313	161.133	176.313	78.125	MHz
F_{RXIN2}	RXUSRCLK2(6) maximum frequency	16	16	511.719	511.719	390.625	390.625	322.266	MHz
		16	32	255.859	255.859	195.313	195.313	161.133	MHz
		32	32	511.719	511.719	390.625	390.625	322.266	MHz
		32	64	255.859	255.859	195.313	195.313	161.133	MHz
		64	64	511.719	440.781	402.832	402.832	195.313	MHz
		64	128	255.859	220.391	201.416	201.416	97.656	MHz
		20	20	409.375	409.375	312.500	312.500	257.813	MHz
		20	40	204.688	204.688	156.250	156.250	128.906	MHz
		40	40	409.375	409.375	312.500	350.000	257.813	MHz
		40	80	204.688	204.688	156.250	175.000	128.906	MHz
		80	80	409.375	352.625	322.266	352.625	156.250	MHz
		80	160	204.688	176.313	161.133	176.313	78.125	MHz

Notes:

1. Clocking must be implemented as described in the *UltraScale Architecture GTY Transceiver User Guide* (UG578).
2. For speed grades -3E, -2E, and -2I, a 16-bit and 20-bit internal data path can only be used for line rates less than 8.1875 Gb/s.
3. For speed grade -2LE, a 16-bit and 20-bit internal data path can only be used for line rates less than 8.1875 Gb/s when V_{CCINT} = 0.85V or 6.25 Gb/s when V_{CCINT} = 0.72V.
4. For speed grades -1E and -1I, a 16-bit and 20-bit internal data path can only be used for line rates less than 6.25 Gb/s.
5. For speed grade -1LI, a 16-bit and 20-bit internal data path can only be used for line rates less than 6.25 Gb/s when V_{CCINT} = 0.85V or 5.15625 Gb/s when V_{CCINT} = 0.72V.
6. When the gearbox is used, these maximums refer to the XCLK. For more information, see the *Valid Data Width Combinations for TX Asynchronous Gearbox* table in the *UltraScale Architecture GTY Transceiver User Guide* (UG578).

Table 70: **GTY Transceiver Protocol List *(Cont'd)***

Protocol	Specification	Serial Rate (Gb/s)	Electrical Compliance
Serial RapidIO	RapidIO specification 3.1	1.25–10.3125	Compliant
DisplayPort	DP 1.2B CTS	1.62–5.4	Compliant(3)
Fibre channel	FC-PI-4	1.0625–14.025	Compliant
SATA Gen1, 2, 3	Serial ATA revision 3.0 specification	1.5, 3.0, and 6.0	Compliant
SAS Gen1, 2, 3	T10/BSR INCITS 519	3.0, 6.0, and 12.0	Compliant
SFI-5	OIF-SFI5-01.0	0.625 - 12.5	Compliant
Aurora	CEI-6G, CEI-11G-LR	All rates	Compliant

Notes:

1. 25 dB loss at Nyquist without FEC.
2. The transition time of the transmitter is faster than the IEEE Std 802.3-2012 specification.
3. This protocol requires external circuitry to achieve compliance.

Table 72: **Maximum Performance for Interlaken 6 x 25.78125 Gb/s and 6 x 28.21 Gb/s Protocol and Lane Logic Mode Designs**

Symbol	Description	Speed Grade and V_{CCINT} Operating Voltages										Units
		0.90V		0.85V				0.72V				
		-3(1)		-2(1)		-1		-2		-1		
		Min(2)	Max	Min(2)	Max	Min	Max	Min(2)	Max	Min	Max	
$F_{RX_SERDES_CLK}$	Receive serializer/ deserializer clock	440.79		440.79		N/A		402.84		N/A		MHz
$F_{TX_SERDES_CLK}$	Transmit serializer/ deserializer clock	440.79		440.79		N/A		402.84		N/A		MHz
F_{DRP_CLK}	Dynamic reconfiguration port clock	250.00		250.00		N/A		250.00		N/A		MHz
F_{CORE_CLK}	Interlaken core clock	412.50(3)	479.20	412.50(3)	479.20	N/A		412.50	429.69	N/A		MHz
F_{LBUS_CLK}	Interlaken local bus clock	300.00(4)	349.52	300.00(4)	349.52	N/A		300.00	349.52	N/A		MHz

Notes:

1. 6 x 28.21 mode is only supported in the -2 (V_{CCINT}=0.85V) and -3 (V_{CCINT}=0.90V) speed grades.
2. These are the minimum clock frequencies at the maximum lane performance.
3. The minimum value for CORE_CLK is 451.36 MHz for the 6 x 28.21 Gb/s protocol.
4. The minimum value for LBUS_CLK is 330.00 MHz for the 6 x 28.21 Gb/s protocol.

Table 73: **Maximum Performance for Interlaken 12 x 25.78125 Gb/s Lane Logic Only Mode Designs**

Symbol	Description	Speed Grade and V_{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
$F_{RX_SERDES_CLK}$	Receive serializer/ deserializer clock	402.84	402.84	N/A	N/A	N/A	MHz
$F_{TX_SERDES_CLK}$	Transmit serializer/ deserializer clock	402.84	402.84	N/A	N/A	N/A	MHz
F_{DRP_CLK}	Dynamic reconfiguration port clock	250.00	250.00	N/A	N/A	N/A	MHz
F_{CORE_CLK}	Interlaken core clock	412.50	412.50	N/A	N/A	N/A	MHz
F_{LBUS_CLK}	Interlaken local bus clock	349.52	349.52	N/A	N/A	N/A	MHz

System Monitor Specifications

Table 76: **System Monitor Specifications**

Parameter	Symbol	Comments/Conditions	Min	Typ	Max	Units
V_{CCADC} = 1.8V ±3%, V_{REFP} = 1.25V, V_{REFN} = 0V, ADCCLK = 5.2 MHz, T_j = –40°C to 100°C, typical values at T_j = 40°C						
ADC Accuracy(1)						
Resolution			10	–	–	Bits
Integral nonlinearity(2)	INL		–	–	±1.5	LSBs
Differential nonlinearity	DNL	No missing codes, guaranteed monotonic	–	–	±1	LSBs
Offset error		Offset calibration enabled	–	–	±2	LSBs
Gain error			–	–	±0.4	%
Sample rate			–	–	0.2	MS/s
RMS code noise		External 1.25V reference	–	–	1	LSBs
		On-chip reference	–	1	–	LSBs
ADC Accuracy at Extended Temperatures						
Resolution		T_j = –55°C to 125°C	10	–	–	Bits
Integral nonlinearity(2)	INL	T_j = –55°C to 125°C	–	–	±1.5	LSBs
Differential nonlinearity	DNL	No missing codes, guaranteed monotonic T_j = –55°C to 125°C	–	–	±1	
Analog Inputs(2)						
ADC input ranges		Unipolar operation	0	–	1	V
		Bipolar operation	–0.5	–	+0.5	V
		Unipolar common mode range (FS input)	0	–	+0.5	V
		Bipolar common mode range (FS input)	+0.5	–	+0.6	V
Maximum external channel input ranges		Adjacent channels set within these ranges should not corrupt measurements on adjacent channels	–0.1	–	V_{CCADC}	V
On-Chip Sensor Accuracy						
Temperature sensor error(1)(3)		T_j = –55°C to 125°C (with external REF)	–	–	±3	°C
		T_j = –55°C to 110°C (with internal REF)	–	–	±3.5	°C
		T_j = 110°C to 125°C (with internal REF)	–	–	±5	°C

Revision History

The following table shows the revision history for this document.

Date	Version	Description of Revisions
04/11/2017	1.2	Updated the Summary description. In Table 1, updated and added data, and updated Note 7, added Note 8, Note 9, and Note 10. Updated and added data to Table 2, revised Note 11 and added Note 12 and Note 13. Updated Table 3 and added Note 6. Added specifications to Table 4 though Table 6. Updated maximum V_{ICM} and Note 1 in Table 18. Updated the maximum V_{ODIFF} in Table 19. Updated Table 20, Table 21, and Table 22 to production release for the following devices/speed/temperature grades in Vivado Design Suite 2017.1. XCKU3P: -2E, -2I, -1E, -1I XCKU5P: -2E, -2I, -1E, -1I Added Note 1 to Table 21. Updated Table 23. Updated Table 24 and added Note 2. Added Table 25. Updated Table 27 and added Note 3. Many revisions to the speed specifications in Table 28, Table 29, Table 30, Table 33, Table 34, Table 35, Table 40, Table 41, Table 42, Table 43, Table 44, and Table 45. Updated V_L and V_H values in Table 31. In Table 35, added T_{MINPER_CLK} and Note 1, and revised F_{REFCLK}. Added $MMCM_F_{DPRCLK_MAX}$ to Table 38 and $PLL_F_{DPRCLK_MAX}$ to Table 39. Updated Table 46. Revised the GTH Transceiver Specifications and GTH Transceiver Specifications sections. Revised the Integrated Interface Block for Interlaken and Integrated Interface Block for 100G Ethernet MAC and PCS sections. Updated the System Monitor Specifications section including On-Chip Sensor Accuracy and adding Note 3 to Table 76. Removed timing diagrams from the SYSMON I2C/PMBus Interfaces section. Updated the Configuration Switching Characteristics section. Removed the *eFUSE Programming Conditions* table and added the specifications to Table 2 and Table 3. Updated Table 79. Updated the Automotive Applications Disclaimer.
05/09/2016	1.1	In Table 1 revised V_{IN} for HP I/O banks. Updated Note 5 in Table 3. Added values to Table 7. Added MIPI_DPHY_DCI to Table 9, Table 10, and Table 12. Updated and added notes in Table 18 and Table 19. Updated Table 20 speed specifications for Vivado Design Suite 2016.1. Removed Table 23, *Video Codec Unit Performance*. Updated Table 24. Expanded and updated Table 27. Updated Table 28 and Table 29. Updated Table 31 and Table 32 with MIPI D-PHY values. Updated Table 31 and Table 32. In Table 33, added the Block RAM and FIFO Clock-to-Out Delays section. Updated Table 40 to Table 44. Revised the symbol names in Table 43. Revised typical values in Table 48. Updated the -2 (0.72V) and -1 (0.72V) values in Table 50. Added Table 53 and Table 65. Added Note 2 to Table 59. Revised Table 67. Revised data and added notes to Table 62, Table 71, and Table 74. Revised INL in Table 76. Added notes to Table 77 and Table 78. Many revised sections in Table 79.
11/24/2015	1.0	Initial Xilinx release.

Notice of Disclaimer

The information disclosed to you hereunder (the “Materials”) is provided solely for the selection and use of Xilinx products. To the maximum extent permitted by applicable law: (1) Materials are made available "AS IS" and with all faults, Xilinx hereby DISCLAIMS ALL WARRANTIES AND CONDITIONS, EXPRESS, IMPLIED, OR STATUTORY, INCLUDING BUT NOT LIMITED TO WARRANTIES OF MERCHANTABILITY, NON-INFRINGEMENT, OR FITNESS FOR ANY PARTICULAR PURPOSE; and (2) Xilinx shall not be liable (whether in contract or tort, including negligence, or under any other theory of liability) for any loss or damage of any kind or nature related to, arising under, or in connection with, the Materials (including your use of the Materials), including for any direct, indirect, special, incidental, or consequential loss or damage (including loss of data, profits, goodwill, or any type of loss or damage suffered as a result of any action brought by a third party) even if such damage or loss was reasonably foreseeable or Xilinx had been advised of the possibility of the same. Xilinx assumes no obligation to correct any errors contained in the Materials or to notify you of updates to the Materials or to product specifications. You may not reproduce, modify, distribute, or publicly display the Materials without prior written consent. Certain products are subject to the terms and conditions of Xilinx’s limited warranty, please refer to Xilinx’s Terms of Sale which can be viewed at www.xilinx.com/legal.htm#tos; IP cores may be subject to warranty and support terms contained in a license issued to you by Xilinx. Xilinx products are not designed or intended to be fail-safe or for use in any application requiring fail-safe performance; you assume sole risk and liability for use of Xilinx products in such critical applications, please refer to Xilinx’s Terms of Sale which can be viewed at www.xilinx.com/legal.htm#tos.

Automotive Applications Disclaimer

AUTOMOTIVE PRODUCTS (IDENTIFIED AS "XA" IN THE PART NUMBER) ARE NOT WARRANTED FOR USE IN THE DEPLOYMENT OF AIRBAGS OR FOR USE IN APPLICATIONS THAT AFFECT CONTROL OF A VEHICLE ("SAFETY APPLICATION") UNLESS THERE IS A SAFETY CONCEPT OR REDUNDANCY FEATURE CONSISTENT WITH THE ISO 26262 AUTOMOTIVE SAFETY STANDARD ("SAFETY DESIGN"). CUSTOMER SHALL, PRIOR TO USING OR DISTRIBUTING ANY SYSTEMS THAT INCORPORATE PRODUCTS, THOROUGHLY TEST SUCH SYSTEMS FOR SAFETY PURPOSES. USE OF PRODUCTS IN A SAFETY APPLICATION WITHOUT A SAFETY DESIGN IS FULLY AT THE RISK OF CUSTOMER, SUBJECT ONLY TO APPLICABLE LAWS AND REGULATIONS GOVERNING LIMITATIONS ON PRODUCT LIABILITY.